

1N6267A Series

1500 Watt Mosorb™ Zener Transient Voltage Suppressors

Unidirectional

Mosorb devices are designed to protect voltage sensitive components from high voltage, high-energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. These devices are ON Semiconductor's exclusive, cost-effective, highly reliable Surmetic™ axial leaded package and are ideally-suited for use in communication systems, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications, to protect CMOS, MOS and Bipolar integrated circuits.

Features

- Working Peak Reverse Voltage Range - 5.8 V to 214 V
- Peak Power - 1500 Watts @ 1 ms
- ESD Rating of Class 3 (>16 kV) per Human Body Model
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage < 5 μ A Above 10 V
- UL 497B for Isolated Loop Circuit Protection
- Response Time is Typically < 1 ns
- Pb-Free Packages are Available*

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 260°C, 1/16 in from the case for 10 seconds

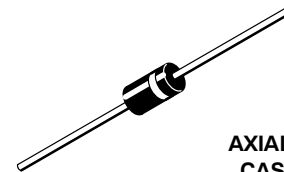
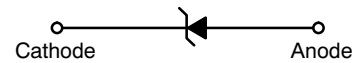
POLARITY: Cathode indicated by polarity band

MOUNTING POSITION: Any



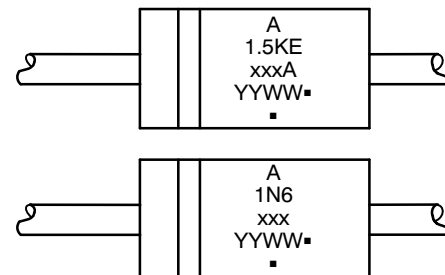
ON Semiconductor®

<http://onsemi.com>



**AXIAL LEAD
CASE 41A
PLASTIC**

MARKING DIAGRAMS



A = Assembly Location
1.5KExxxA = ON Device Code
1N6xxx = JEDEC Device Code
YY = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
1.5KExxxAG	Axial Lead (Pb-Free)	500 Units/Box
1.5KExxxARL4G	Axial Lead (Pb-Free)	1500/Tape & Reel
1N6xxxAG	Axial Lead (Pb-Free)	500 Units/Box
1N6xxxARL4G	Axial Lead (Pb-Free)	1500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS

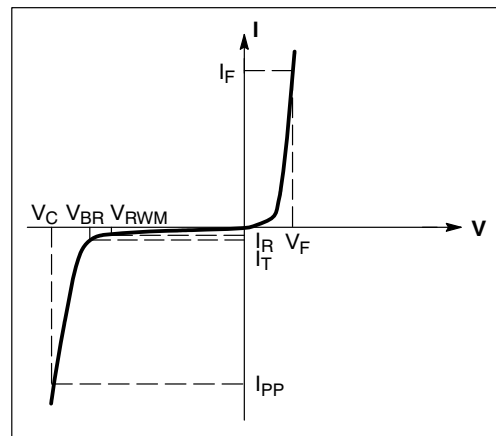
Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ $T_L \leq 25^\circ\text{C}$	P_{PK}	1500	W
Steady State Power Dissipation @ $T_L \leq 75^\circ\text{C}$, Lead Length = 3/8 in Derated above $T_L = 75^\circ\text{C}$	P_D	5.0	W
		20	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Lead	$R_{\theta JL}$	20	$^\circ\text{C/W}$
Forward Surge Current (Note 2) @ $T_A = 25^\circ\text{C}$	I_{FSM}	200	A
Operating and Storage Temperature Range	T_J, T_{stg}	- 65 to +175	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Nonrepetitive current pulse per Figure 5 and derated above $T_A = 25^\circ\text{C}$ per Figure 2.
2. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 3.5\text{ V Max.}$, I_F (Note 3) = 100 A)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F



Uni-Directional TVS

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 3.5\text{ V Max.}$ @ I_F (Note 3) = 100 A)

Device†	JEDEC Device† (Note 4)	V_{RWM} (Note 5) (Volts)	I_R @ V_{RWM} (μA)	Breakdown Voltage			V_C @ I_{PP} (Note 7)		Θ_{VBR} (%/°C)	
				V_{BR} (Note 6) (Volts)			$@ I_T$ (mA)	V_C (Volts)		I_{PP} (A)
				Min	Nom	Max				
1.5KE6.8AG	1N6267AG	5.8	1000	6.45	6.8	7.14	10	10.5	143	0.057
1.5KE7.5AG	-	6.4	500	7.13	7.5	7.88	10	11.3	132	0.061
1.5KE8.2AG	1N6269AG	7.02	200	7.79	8.2	8.61	10	12.1	124	0.065
1.5KE9.1AG	-	7.78	50	8.65	9.1	9.55	1	13.4	112	0.068
1.5KE10AG	1N6271AG	8.55	10	9.5	10	10.5	1	14.5	103	0.073
1.5KE11AG	-	9.4	5	10.5	11	11.6	1	15.6	96	0.075
1.5KE12AG	-	10.2	5	11.4	12	12.6	1	16.7	90	0.078
1.5KE13AG	1N6274AG	11.1	5	12.4	13	13.7	1	18.2	82	0.081
1.5KE15AG	1N6275AG	12.8	5	14.3	15	15.8	1	21.2	71	0.084
1.5KE16A, G	1N6276AG	13.6	5	15.2	16	16.8	1	22.5	67	0.086
1.5KE18A, G	1N6277AG	15.3	5	17.1	18	18.9	1	25.2	59.5	0.088
1.5KE20AG	1N6278AG	17.1	5	19	20	21	1	27.7	54	0.09
-	1N6279AG	18.8	5	20.9	22	23.1	1	30.6	49	0.092
1.5KE24AG	1N6280AG	20.5	5	22.8	24	25.2	1	33.2	45	0.094
1.5KE27AG	1N6281AG	23.1	5	25.7	27	28.4	1	37.5	40	0.096
1.5KE30AG	1N6282AG	25.6	5	28.5	30	31.5	1	41.4	36	0.097
1.5KE33AG	1N6283AG	28.2	5	31.4	33	34.7	1	45.7	33	0.098
1.5KE36AG	1N6284AG	30.8	5	34.2	36	37.8	1	49.9	30	0.099
1.5KE39AG	1N6285AG	33.3	5	37.1	39	41	1	53.9	28	0.1
1.5KE43AG	1N6286AG	36.8	5	40.9	43	45.2	1	59.3	25.3	0.101
1.5KE47AG	1N6287AG	40.2	5	44.7	47	49.4	1	64.8	23.2	0.101
1.5KE51AG	1N6288A, G	43.6	5	48.5	51	53.6	1	70.1	21.4	0.102
1.5KE56AG	1N6289AG	47.8	5	53.2	56	58.8	1	77	19.5	0.103
1.5KE62AG	1N6290AG	53	5	58.9	62	65.1	1	85	17.7	0.104
1.5KE68AG	1N6291AG	58.1	5	64.6	68	71.4	1	92	16.3	0.104
1.5KE75AG	1N6292AG	64.1	5	71.3	75	78.8	1	103	14.6	0.105
1.5KE82A, G	-	70.1	5	77.9	82	86.1	1	113	13.3	0.105
1.5KE91AG	1N6294AG	77.8	5	86.5	91	95.5	1	125	12	0.106
-	1N6295AG	85.5	5	95	100	105	1	137	11	0.106

Devices listed in **bold, italic** are ON Semiconductor Preferred devices. **Preferred** devices are recommended choices for future use and best overall value.

3. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

4. Indicates JEDEC registered data

5. A transient suppressor is normally selected according to the maximum working peak reverse voltage (V_{RWM}), which should be equal to or greater than the dc or continuous peak operating voltage level.

6. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C

7. Surge current waveform per Figure 5 and derate per Figures 1 and 2.

†The "G" suffix indicates Pb-Free package or Pb-Free packages are available.

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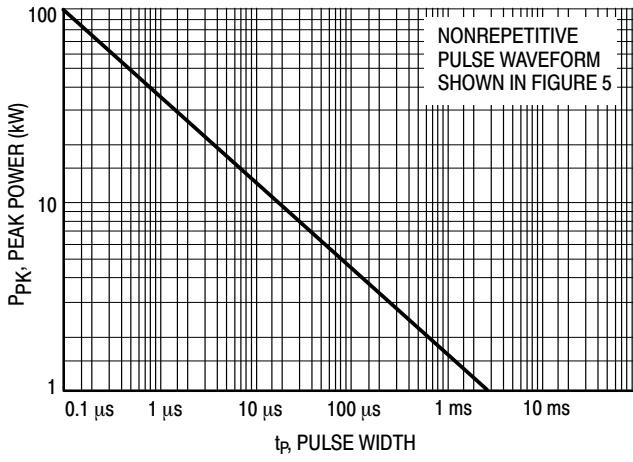


Figure 1. Pulse Rating Curve

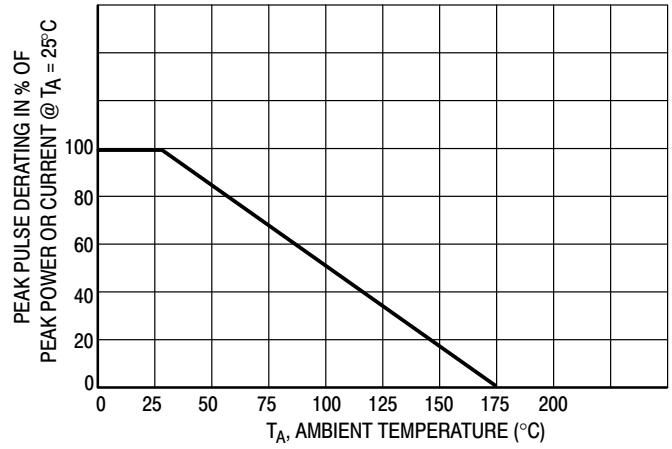


Figure 2. Pulse Derating Curve

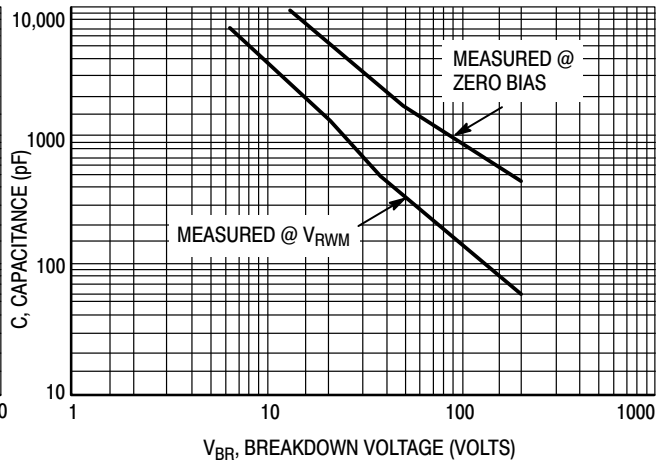
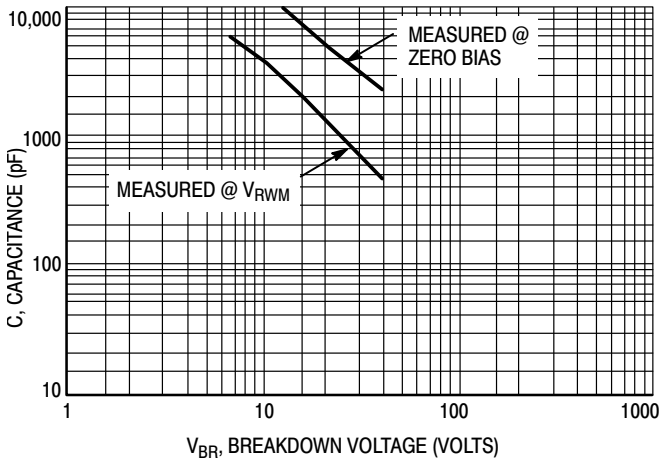


Figure 3. Capacitance versus Breakdown Voltage

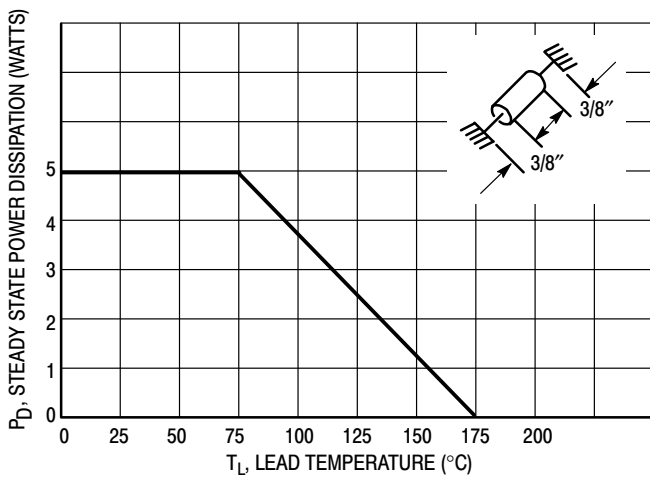


Figure 4. Steady State Power Derating

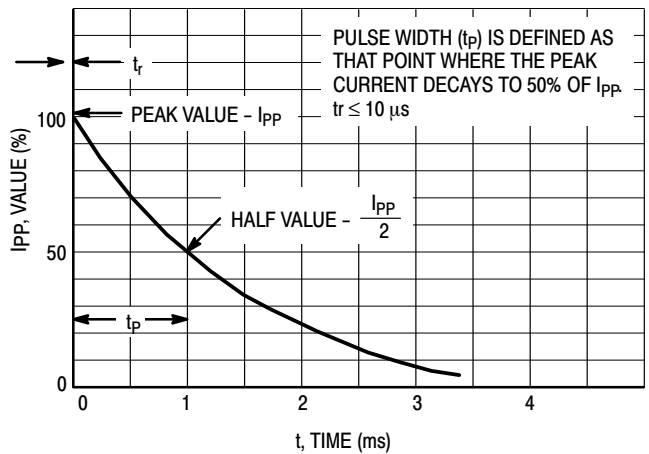


Figure 5. Pulse Waveform

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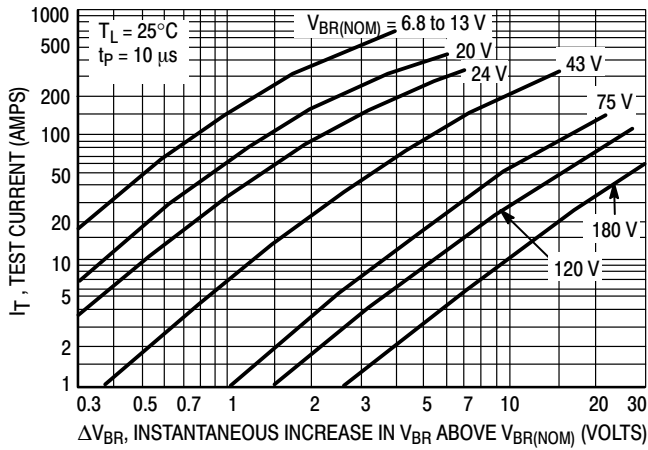


Figure 6. Dynamic Impedance

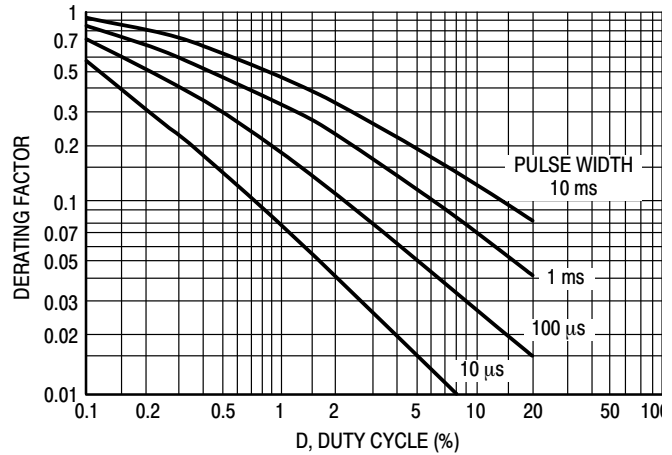


Figure 7. Typical Derating Factor for Duty Cycle

APPLICATION NOTES

RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitance effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 8.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 9. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. These devices have excellent response time, typically in the picosecond range and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper

circuit layout, minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by Z_{in} is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

DUTY CYCLE DERATING

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 7. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 7 appear to be in error as the 10 ms pulse has a higher derating factor than the 10 μs pulse. However, when the derating factor for a given pulse of Figure 7 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.

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TYPICAL PROTECTION CIRCUIT

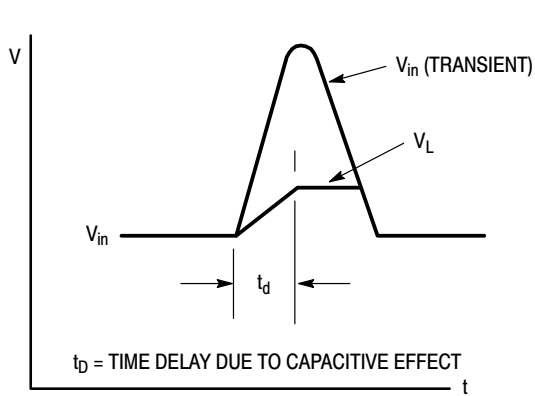
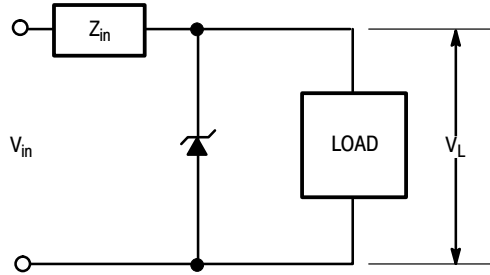


Figure 8.

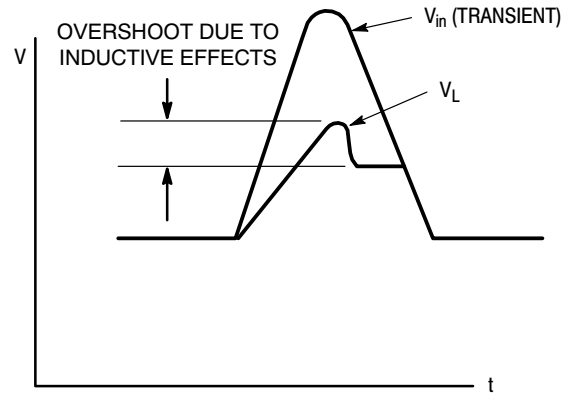


Figure 9.

UL RECOGNITION*

The entire series has *Underwriters Laboratory Recognition* for the classification of protectors (QVGV2) under the UL standard for safety 497B and File #E210057. Many competitors only have one or two devices recognized or have recognition in a non-protective category. Some competitors have no recognition at all. With the UL497B recognition, our parts successfully passed several tests including Strike Voltage Breakdown test, Endurance

Conditioning, Temperature test, Dielectric Voltage-Withstand test, Discharge test and several more.

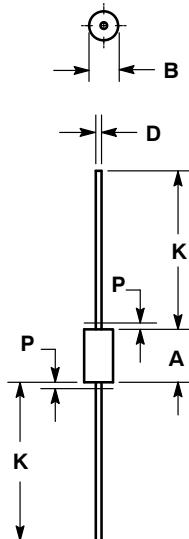
Whereas, some competitors have only passed a flammability test for the package material, we have been recognized for much more to be included in their Protector category.

*Applies to 1.5KE6.8A thru 1.5KE250A

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PACKAGE DIMENSIONS

MOSORB CASE 41A-04 ISSUE D



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. LEAD FINISH AND DIAMETER UNCONTROLLED IN DIMENSION P.
4. 041A-01 THRU 041A-03 OBSOLETE, NEW STANDARD 041A-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.374	8.50	9.50
B	0.189	0.209	4.80	5.30
D	0.038	0.042	0.96	1.06
K	1.000	---	25.40	---
P	---	0.050	---	1.27

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